FORM: PTO-1449 (REV: 7-80)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			Atty Docket No:	Serial No:	2
(REV: /-80	0)	PA	AIENI AND	TRADEMARK OFFICE	2000-0133.00 Applicant:	Uni	cnown L
INFOR	MATIO	ON DISCLOSI	URE STATE	MENT BY APPLICANT	Kelly T. Hurley		55.
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(37 CFR 1.98(b))		(use several sheets if necessary)		l sheets if necessary)	Concurrently Herewith	Unk	cnown E
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	AM AN AO AP	Number	Date	Country  CHER ART (including author	Class , title, date, pertinent pages	, etc.)	Yes No
Initial	AM AN AO AP AQ	Number	Date OT Novel 0.44µm²	Country  CHER ART (including author Ti-Salicide STI Cell Technolo	Class , title, date, pertinent pages gy for High Density NOR F	, etc.)	Yes No
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication with applicant.